



Cite this: *Phys. Chem. Chem. Phys.*,  
2016, **18**, 14139

## Correction: The effect of recombination under short-circuit conditions on the determination of charge transport properties in nanostructured photoelectrodes

J. Villanueva-Cab,<sup>\*a</sup> J. A. Anta<sup>b</sup> and G. Oskam<sup>c</sup>

DOI: 10.1039/c6cp90121b

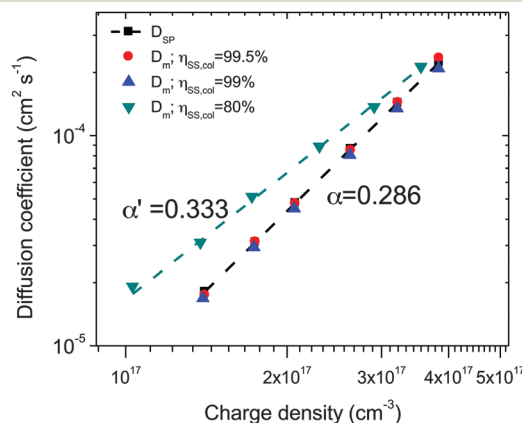
www.rsc.org/pccp

Correction for 'The effect of recombination under short-circuit conditions on the determination of charge transport properties in nanostructured photoelectrodes' by J. Villanueva-Cab *et al.*, *Phys. Chem. Chem. Phys.*, 2016, **18**, 2303–2308.

On page 2304 of the published article, eqn (1) should be amended as shown below:

$$\frac{\partial n}{\partial t} = \frac{\partial}{\partial x} \left[ D_0 (n/n_0)^{(1-\alpha)/\alpha} \frac{\partial n}{\partial x} \right] + G(x) - k_0 (n/n_0)^{(\beta-\alpha)/\alpha} n \quad (1)$$

In addition, Fig. 2 in the published article should be replaced with the revised version below:



**Fig. 2** Diffusion coefficient as function of charge density. Comparison between measured (SLIT) values and the model predictions for three different recombination rate constants:  $k_0 = 0$  ( $\eta_{SS, coll} = 99.5\%$  at 1 Sun),  $k_0 = 2.718 \times 10^{-3} \text{ s}^{-1}$  ( $\eta_{SS, coll} = 99\%$  at 1 Sun) and  $k_0 = 0.12 \text{ s}^{-1}$  ( $\eta_{SS, coll} = 80\%$  at 1 Sun). When recombination takes place under short circuit conditions, the diffusion coefficient is overestimated, which can be erroneously interpreted as a trap distribution of  $\alpha' = 0.333$ . See the text for details.

The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.

<sup>a</sup> Instituto de Física, Benemérita Universidad Autónoma de Puebla, Apdo. Postal J-48, Puebla, Pue. 72570, Mexico. E-mail: juliovc@ifuap.buap.mx

<sup>b</sup> Nanostructured Solar Cells Group, Department of Physical, Chemical and Natural Systems, Universidad Pablo de Olavide, Ctra. Utrera, km 1, ES-41013 Seville, Spain

<sup>c</sup> Departamento de Física Aplicada, CINVESTAV-IPN, Mérida, Yuc. 97310, Mexico

